



# 60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
60V	$50mΩ @ V_{GS} = 10V$	24A
60 V	65mΩ @ V <sub>GS</sub> = 4.5V	21A

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

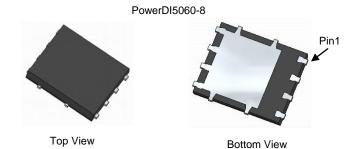
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

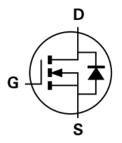
### **Features and Benefits**

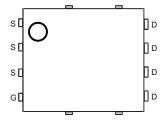
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Minimizes Power Losses
- Low Q<sub>g</sub> Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.097 grams (Approximate)







Internal Schematic

Top View Pin Configuration

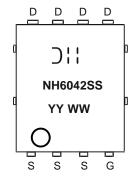
#### Ordering Information (Note 5)

Part Number	Case	Packaging	
DMNH6042SPSQ-13	PowerDI5060-8	2500/Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



);; = Manufacturer's Marking
NH6042SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)



# 

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	60	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 8) $V_{GS} = 10V$ Steady $T_{C} = +25^{\circ}C$ State $T_{C} = +100^{\circ}C$			I <sub>D</sub>	24 17	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	35	Α
Maximum Continuous Body Diode Forward Current (Note 8)			Is	24	Α
Avalanche Current (Note 9) L = 10mH			I <sub>AS</sub>	3.5	Α
Avalanche Energy (Note 9) L = 10mH			E <sub>AS</sub>	65	mJ

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		$P_D$	1.5	W
Thermal Decistores, Junction to Ambient (Note C)	Steady state	7	98	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	54	10/00
Total Power Dissipation (Note 7)		P <sub>D</sub>	2.9	W
Thermal Decistones, Junction to Ambient (Note 7)	Steady state	7	51	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{\theta JA}$	26	
Thermal Resistance, Junction to Case (Note 8)	$R_{\theta JC}$	3.5		
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +175	°C	

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

<u></u>							
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	-	_	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	1	3.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		I	34	50	mΩ	$V_{GS} = 10V, I_D = 5.1A$	
Static Dialit-Source Off-Resistance	R <sub>DS(ON)</sub>	1	45	65	11122	$V_{GS} = 4.5V, I_D = 4.4A$	
Diode Forward Voltage	$V_{SD}$	l	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 2.6A$	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	Ciss	1	584	_	pF	25)( )( 2)(	
Output Capacitance	Coss	l	83	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	I	24	_	pF	1 – 1.0101112	
Gate Resistance	$R_g$	I	3.8	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_g$	I	4.2	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	I	8.8	_	nC	V <sub>DS</sub> = 44V. I <sub>D</sub> = 5.2A	
Gate-Source Charge	$Q_{gs}$	I	1.8	_	nC	$V_{DS} = 44V, I_{D} = 5.2A$	
Gate-Drain Charge	$Q_{gd}$	1	1.8	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.4	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	1.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_G = 6\Omega, I_D = 1A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	10.1	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	4.5	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>		12.9	_	ns	I <sub>F</sub> = 2.6A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge		_	5.4	_	nC	$I_F = 2.6A$ , $di/dt = 100A/\mu s$	

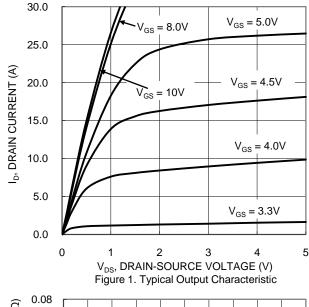
6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

<sup>7.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

<sup>8.</sup> Thermal resistance from junction to soldering point (on the exposed drain pad).

I. As and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





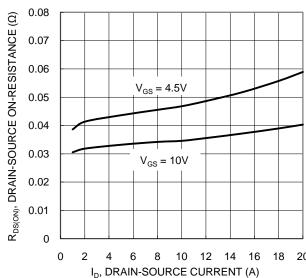


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

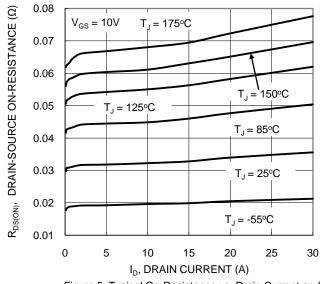
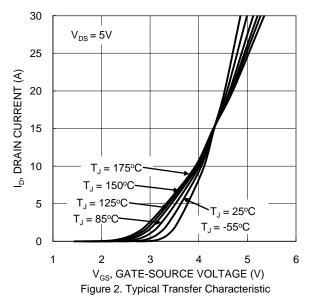
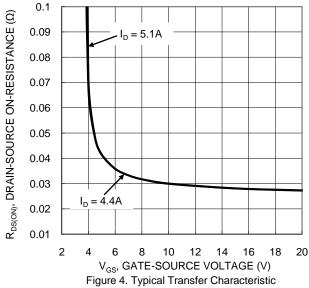


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





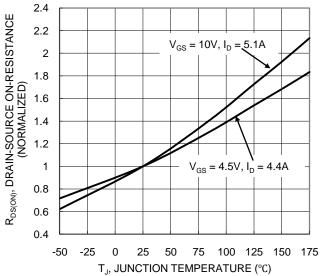
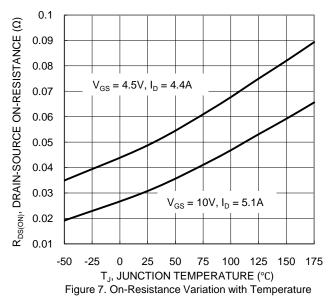
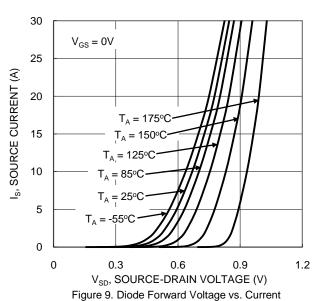


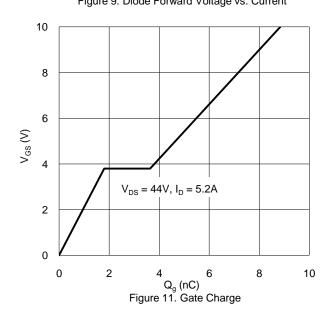
Figure 6. On-Resistance Variation with Temperature











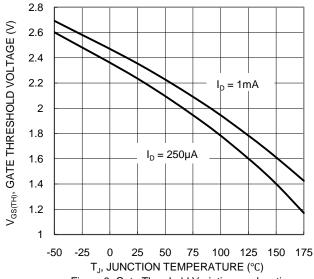
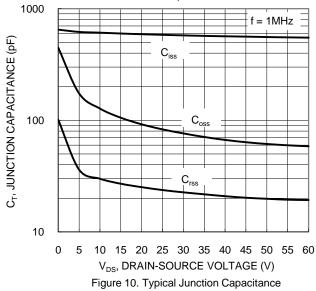
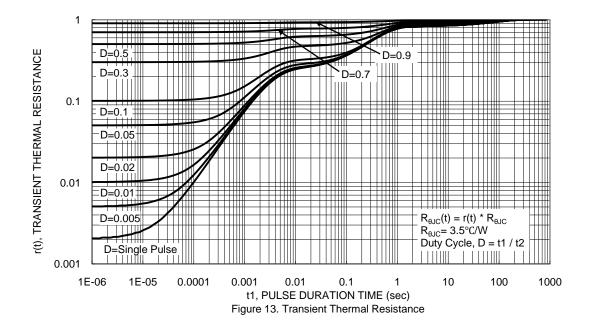


Figure 8. Gate Threshold Variation vs. Junction Temperature



100  $R_{DS(ON)}$  Limited 10 ID, DRAIN CURRENT (A) P<sub>w</sub>=10ms 1 P<sub>W</sub>=100ms  $T_{J(Max)} = 175$ °C 0.1 T<sub>C</sub>=25°C Single Pulse DUT on infinite heatsink V<sub>GS</sub>=10V 0.01 0.1 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



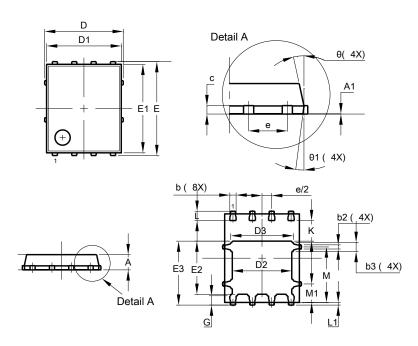




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

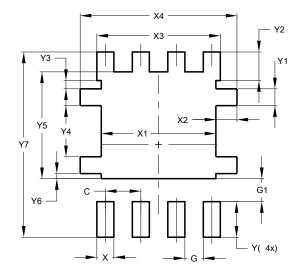


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	,	5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(	6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12º	11º		
Θ1	6º	8º	7º		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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